



US009570527B2

(12) **United States Patent**
Namkung

(10) **Patent No.:** **US 9,570,527 B2**
(45) **Date of Patent:** **Feb. 14, 2017**

(54) **ORGANIC LIGHT EMITTING DIODE DISPLAY**

(71) Applicant: **Samsung Display Co., Ltd., Yongin (KR)**

(72) Inventor: **Jun Namkung, Yongin (KR)**

(73) Assignee: **Samsung Display Co., Ltd., Yongin-si (KR)**

(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 75 days.

(21) Appl. No.: **14/063,702**

(22) Filed: **Oct. 25, 2013**

(65) **Prior Publication Data**

US 2015/0001477 A1 Jan. 1, 2015

(51) **Int. Cl.**
H01L 27/32 (2006.01)

(52) **U.S. Cl.**
CPC ... **H01L 27/3258** (2013.01); **H01L 2251/5338** (2013.01)

(58) **Field of Classification Search**
CPC H01L 27/28; H01L 27/32; H01L 27/3211; H01L 27/3216; H01L 27/3218; H01L 27/3258; H01L 27/326; H01L 51/5203; H01L 51/5209; H01L 51/5225
See application file for complete search history.

(56) **References Cited**

U.S. PATENT DOCUMENTS

8,229,522 B2 7/2012 Kim et al.
2010/0109511 A1* 5/2010 Kim et al. 313/504

2010/0327297 A1* 12/2010 Yoshida et al. 257/89
2011/0121719 A1* 5/2011 Yokoyama H01L 27/3248
313/504
2013/0001603 A1* 1/2013 Lim et al. 257/88
2013/0002133 A1* 1/2013 Jin et al. 313/511
2013/0099258 A1* 4/2013 Lim et al. 257/88
2014/0312319 A1* 10/2014 Kim 257/40
2016/0021718 A1* 1/2016 Kikuchi H01L 51/5271
362/231

FOREIGN PATENT DOCUMENTS

JP 10-233982 9/1998
KR 10-2001-0009748 2/2001

* cited by examiner

Primary Examiner — Stephen W Smoot

Assistant Examiner — Sun M Kim

(74) *Attorney, Agent, or Firm* — H.C. Park & Associates, PLC

(57) **ABSTRACT**

An organic light emitting diode display may include a front display part including a plurality of front pixels formed on a substrate and realizing an image at a front and a side display part. A side pixel of the side display part may include: a plurality of thin film transistors formed on the substrate; a protective layer covering the plurality of thin film transistor and having an inclination groove that is oblique; a first electrode formed at the inclination groove of the protective layer; a pixel defining layer having an opening exposing the first electrode and formed on the protective layer; an organic emission layer formed on the first electrode and the pixel defining layer; and a second electrode covering the organic emission layer.

17 Claims, 9 Drawing Sheets

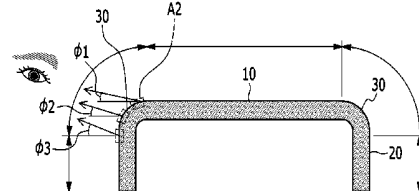
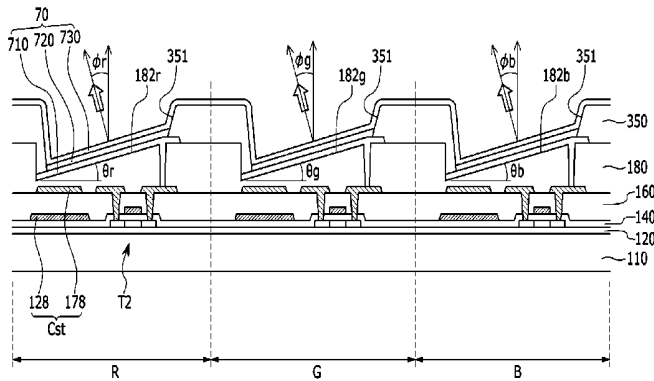


FIG. 1

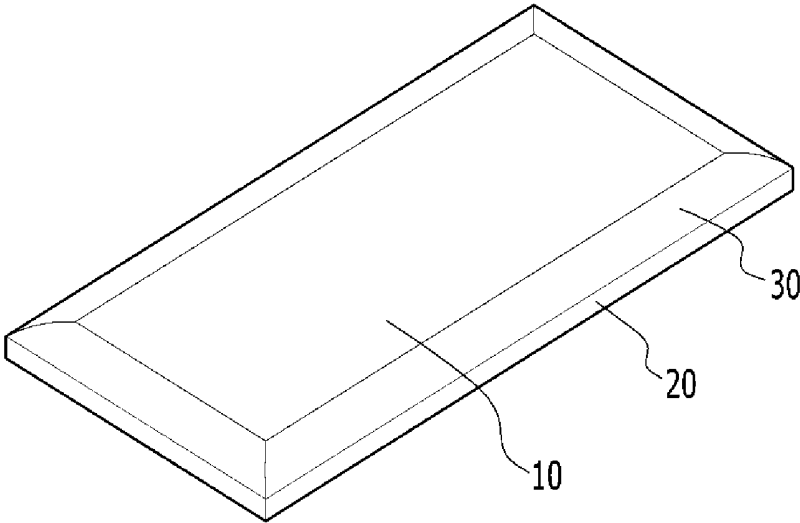


FIG. 2

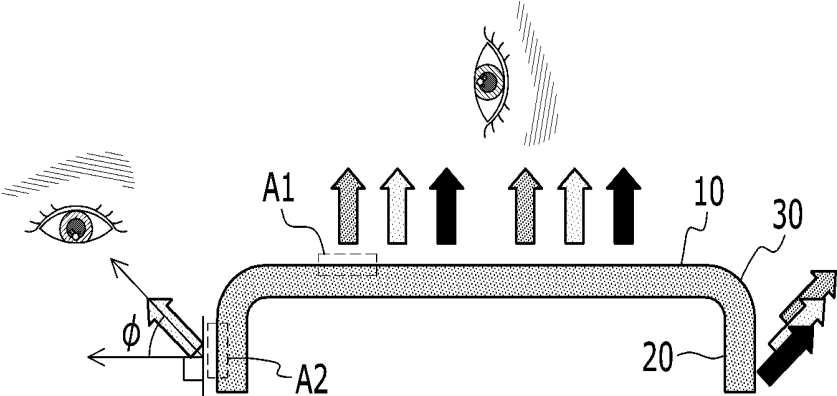


FIG. 3

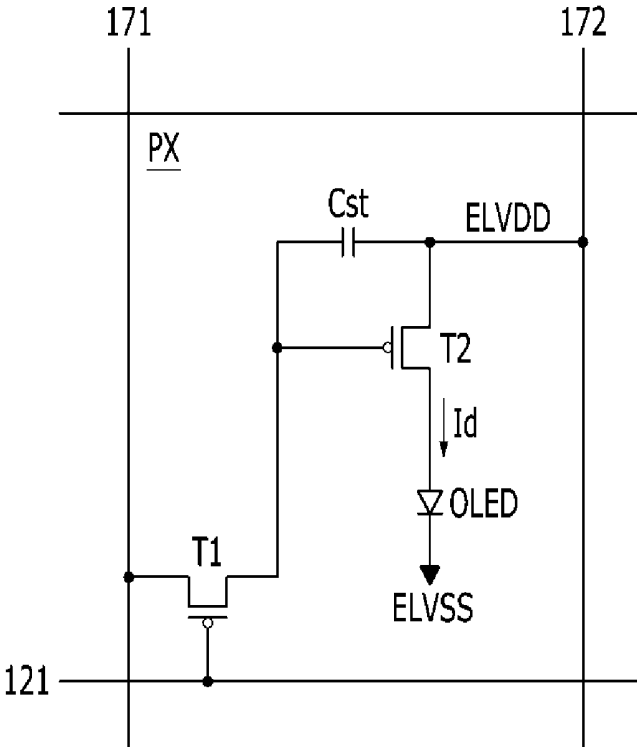


FIG. 4

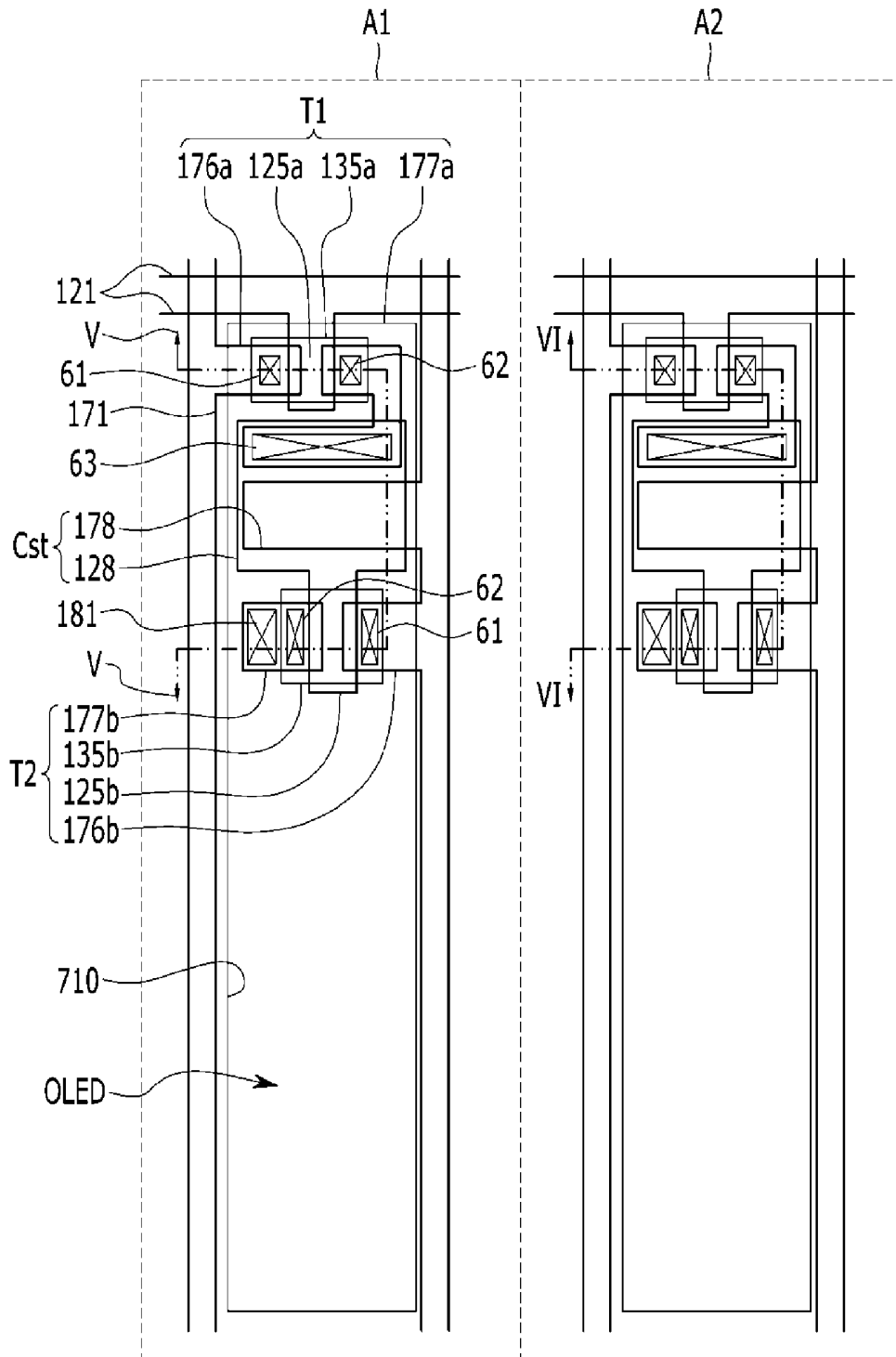


FIG. 5

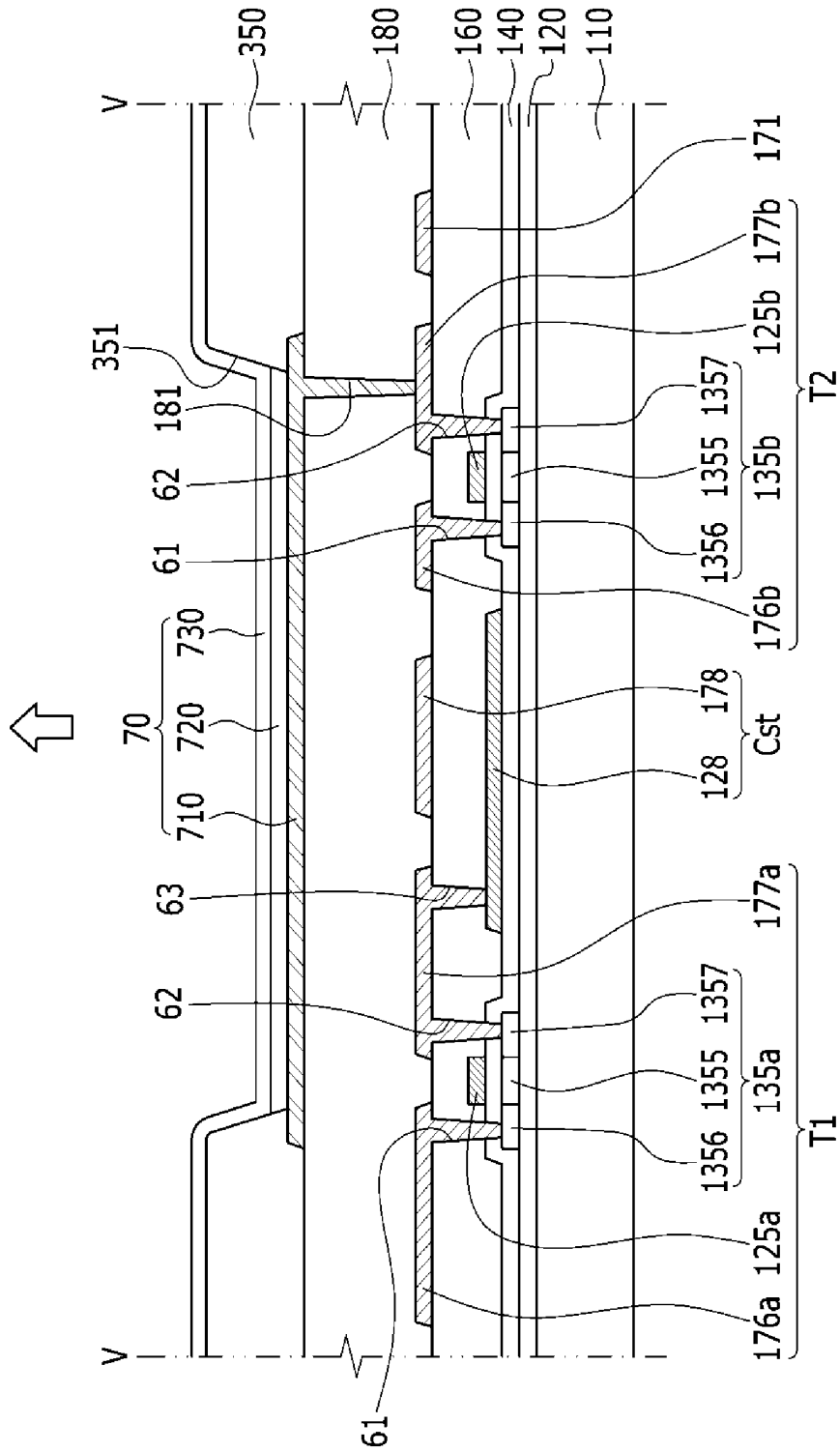


FIG. 6

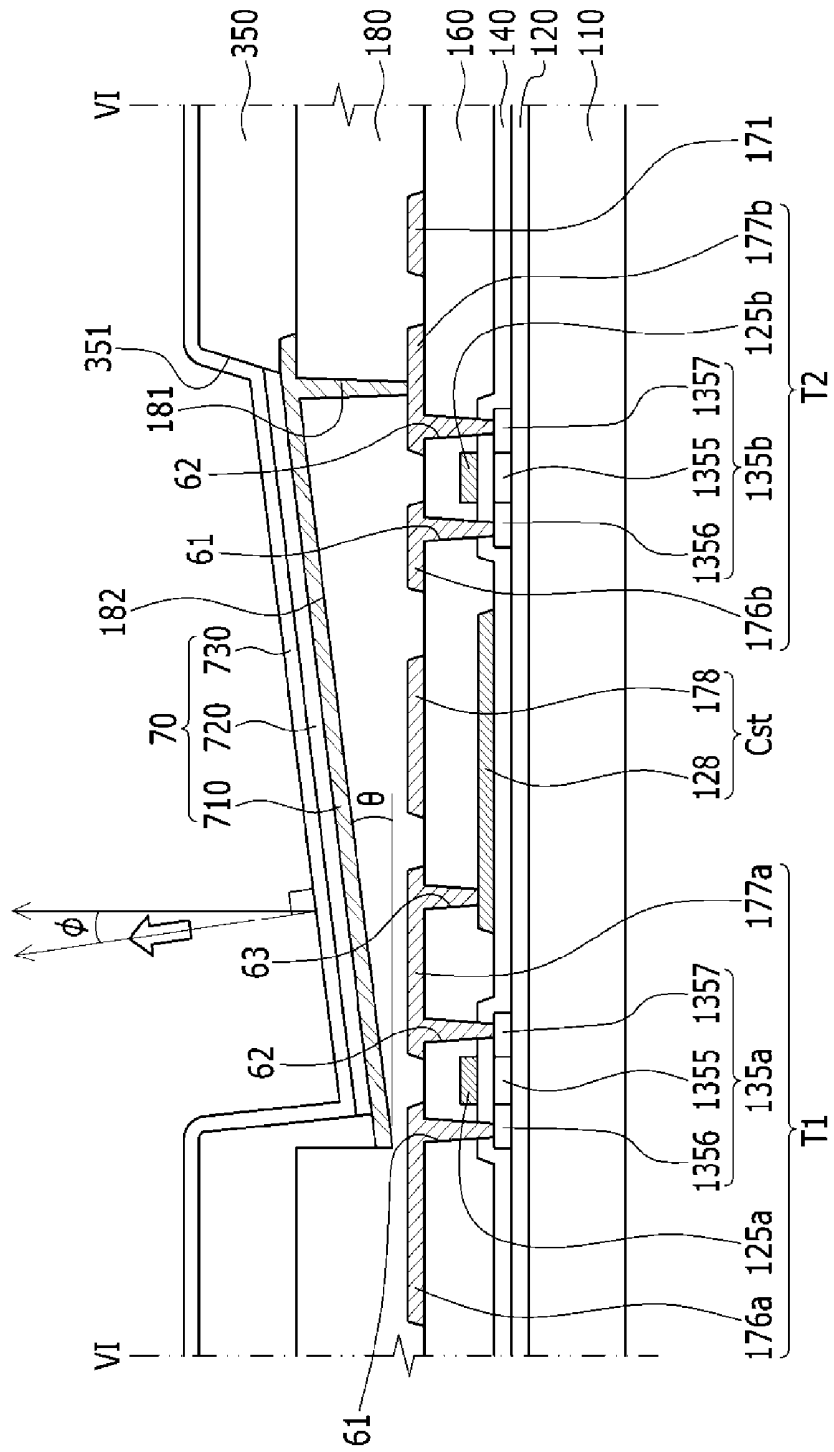


FIG. 7

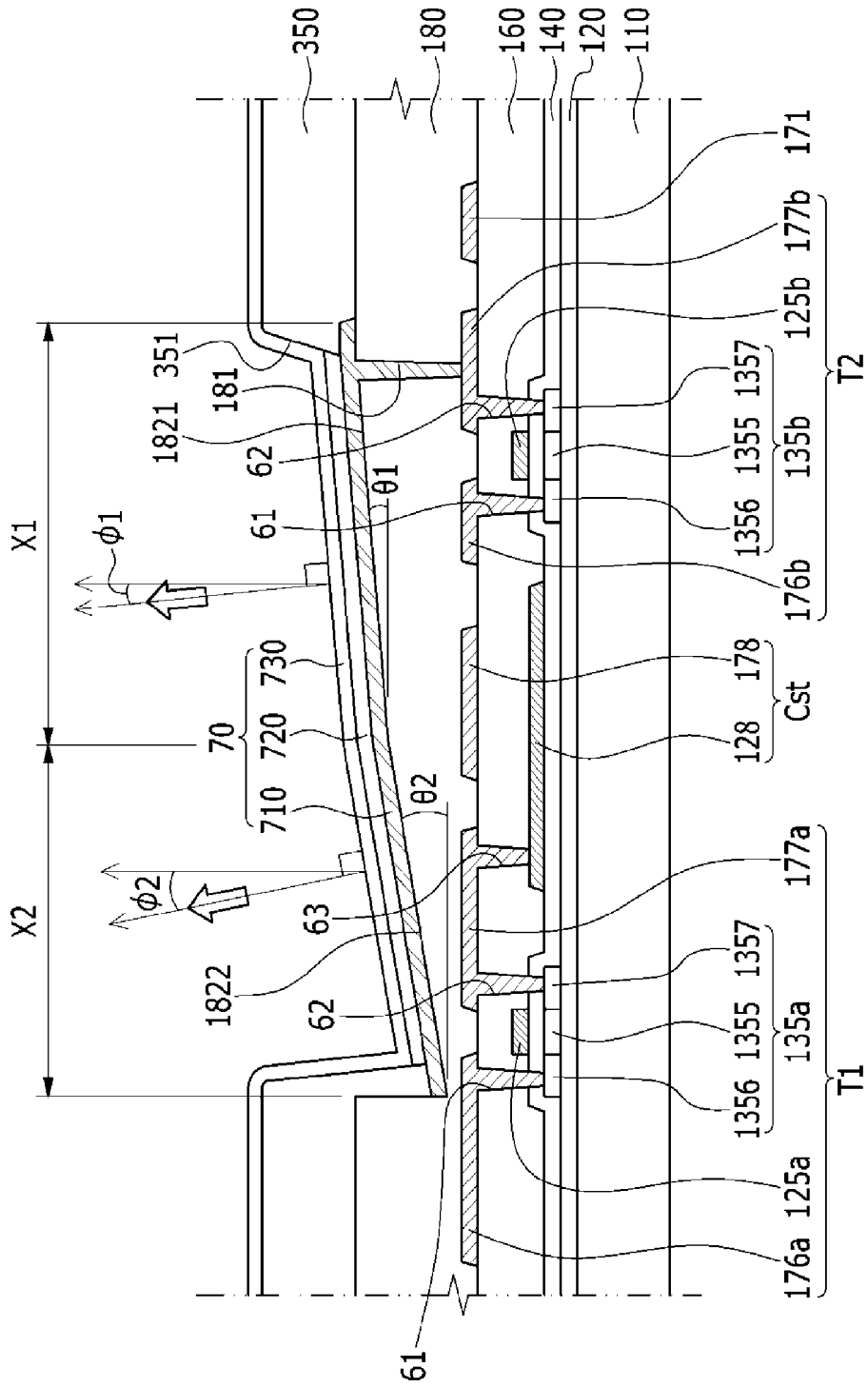


FIG. 8

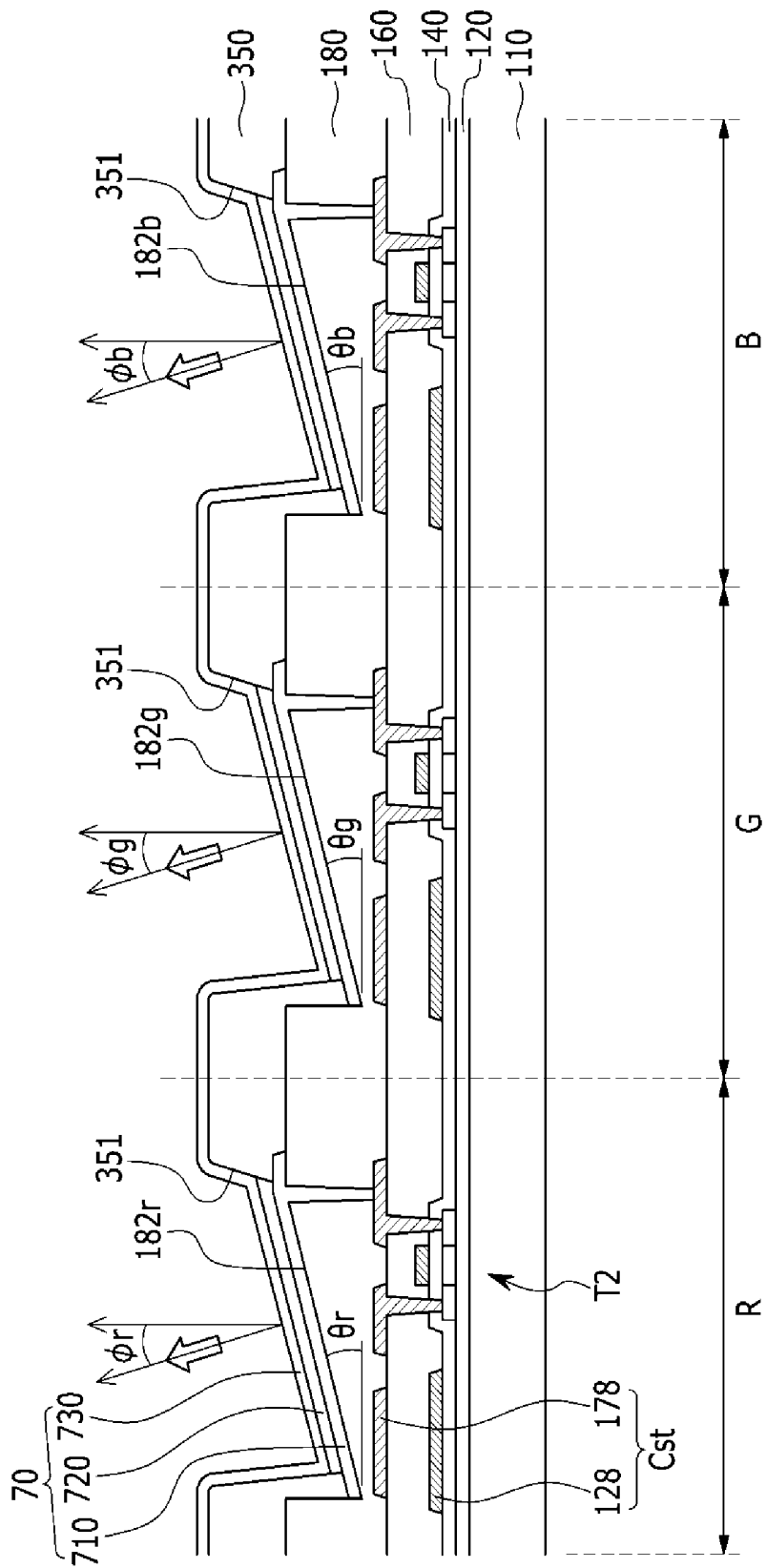
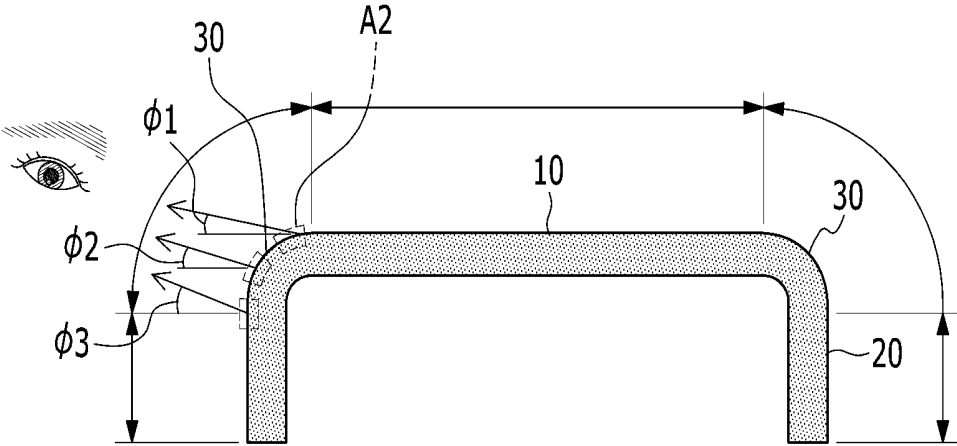


FIG. 9



ORGANIC LIGHT EMITTING DIODE DISPLAY

CROSS REFERENCE TO RELATED APPLICATION

This application claims priority from and the benefit of Korean Patent Application No. 10-2013-0076610, filed on Jul. 1, 2013, which is hereby incorporated by reference for all purposes as if fully set forth herein.

BACKGROUND

Field

Exemplary embodiments of the present disclosure relate to an organic light emitting diode (OLED) display.

Description of the Background

An organic light emitting diode display includes two electrodes and an organic light emitting member disposed therebetween. Electrons injected from one electrode and holes is injected from the other electrode are combined in the organic light emitting member to form excitons, and light is emitted as the excitons release energy.

For applying the OLED display to various types of applications, a flexible OLED display is manufactured to be flexible. In flexible OLED displays, a bendable OLED display is bent at an edge, thereby having a structure in which a front display part is realized without dead space and simultaneously a side display part that can be visible at a side is realized.

However, the bendable OLED display is manufactured with reference to the front display part such that maximum luminance may be obtained at a viewing angle of 0 degrees, that is, at the front side, but the luminance is sharply deteriorated at the bending display part.

The above information disclosed in this Background section is provided to enhance understanding of the background of the present disclosure and therefore may contain information that does not form prior art that is already known to a person of ordinary skill in the art.

SUMMARY

Exemplary embodiments of the present disclosure provide an organic light emitting diode (OLED) display with improved luminance of a side display part.

Additional features of the present disclosure will be set forth in the description which follows, and in part will be apparent from the description, or may be learned by practice of the disclosed subject matter.

Exemplary embodiments of the present disclosure disclose an organic light emitting diode (OLED) display including a front display part and a side display part. The front display part includes a plurality of front pixels configured to provide an image at a first side of is the OLED display. The side display part includes a plurality of side pixels configured to provide the image at a second side of the OLED display. Each side pixel includes: a plurality of thin film transistors; a protective layer covering the plurality of thin film transistors and having an oblique inclination groove; a first electrode formed at the inclination groove; a pixel definition layer disposed on the protective layer and having an opening exposing the first electrode; an organic emission layer disposed on the first electrode and the pixel definition layer; and a second electrode disposed on the organic emission layer. A side OLED includes the first

electrode, the organic emission layer, and the second electrode, and is configured to be oblique.

Exemplary embodiments of the present disclosure also disclose a pixel. The pixel includes at least one switching element, a protective layer, and an organic light emitting diode. The protective layer is disposed on the at least one switching element. The protective layer has a top surface inclined at an inclination angle relative to a bottom surface of the protective layer. The OLED is disposed on the protective layer and includes a bottom electrode. The bottom electrode is inclined at the inclination angle and is connected to the at least one switching element.

Exemplary embodiments of the present disclosure also disclose an organic light emitting diode (OLED) display including a front display part, a side display part, and a bending display part connecting the front display part and the side display part. Each of the front display part, the side display part, and the bending display part includes a plurality of pixels. Each of the pixels includes at least one switching element, a protective layer disposed on the at least one switching element, and an OLED disposed on the protective layer. In pixels of the front display part, a top surface of the OLED is parallel to a surface of the protective layer. In a pixel of the side display part or the bending display part, a top surface of the protective layer is inclined at an is inclination angle with respect to a bottom surface of the protective layer, and a top surface of the OLED is inclined with respect to the bottom surface of the protective layer.

Exemplary embodiments of the present disclosure also disclose an organic light emitting diode (OLED) display including a front display part, a side display part, and a bending display part connecting the front display part and the side display part. The front display part includes a plurality of first pixels, and the side display part and the bending display part includes a plurality of second pixels. Each of the plurality of second pixels includes an OLED with an inclined surface. An inclination angle of the inclined surface corresponds to a location of the OLED.

It is to be understood that both the foregoing general description and the following detailed description are exemplary and explanatory and are intended to provide further explanation of the disclosed subject matter as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

The accompanying drawings, which are included to provide a further understanding of the disclosed subject matter and are incorporated in and constitute a part of this specification, illustrate exemplary embodiments of the disclosed subject matter, and together with the description serve to explain the principles of the disclosed subject matter.

FIG. 1 is a perspective view of an OLED display according to exemplary embodiments of the present disclosure.

FIG. 2 is a side view of an OLED display according to exemplary embodiments of the present disclosure.

FIG. 3 is an equivalent circuit of one pixel of an OLED display according to is exemplary embodiments of the present disclosure.

FIG. 4 is a layout view of one pixel respectively positioned at a front display part and a side display part of an OLED display according to exemplary embodiments of the present disclosure.

FIG. 5 is a cross-sectional view taken along the line V-V of FIG. 4 according to exemplary embodiments of the present disclosure.

FIG. 6 is a cross-sectional view taken along the line VI-VI of FIG. 4 according to exemplary embodiments of the present disclosure.

FIG. 7 is a cross-sectional view of a side pixel positioned at a side display part of an OLED display according to exemplary embodiments of the present disclosure.

FIG. 8 is a cross-sectional view of a side red pixel, a side green pixel, and a side blue pixel of a side pixel positioned at a side display part of an OLED display according to exemplary embodiments of the present disclosure.

FIG. 9 is a side view of an OLED display according to exemplary embodiments of the present disclosure.

DETAILED DESCRIPTION OF THE ILLUSTRATED EMBODIMENTS

The disclosed subject matter is described more fully hereinafter with reference to the accompanying drawings, in which exemplary embodiments of the disclosed subject matter are shown. This disclosed subject matter may, however, be embodied in many different forms and should not be construed as limited to the exemplary embodiments set forth herein. Rather, these exemplary embodiments are provided so that this disclosure is thorough, and will fully convey the scope of the disclosed subject matter to those skilled in the art. In the drawings, the size and relative sizes of layers and regions may be exaggerated for clarity. Like reference numerals in the drawings denote like elements.

It will be understood that when an element or layer is referred to as being “on” or “connected to” another element or layer, it can be directly on or directly connected to the other element or layer, or intervening elements or layers may be present. In contrast, when an element is referred to as being “directly on” or “directly connected to” another element or layer, there are no intervening elements or layers present. It may also be understood that for the purposes of this disclosure, “at least one of X, Y, and Z” can be construed as X only, Y only, Z only, or any combination of two or more items X, Y, and Z (e.g., XYZ, XYY, YZ, ZZ).

It will be understood that, although the terms first, second, third etc. may be used herein to describe various elements, components, regions, layers, and/or sections, these elements, components, regions, layers, and/or sections should not be limited by these terms. These terms are only used to distinguish one element, component, region, layer, or section from another region, layer or section. Thus, a first element, component, region, layer, or section discussed below could be termed a second element, component, region, layer, or section without departing from the teachings of the present disclosure.

Spatially relative terms, such as “beneath”, “below”, “lower”, “above”, “upper”, and the like, may be used herein for ease of description to describe one element or feature’s relationship to another element(s) or feature(s) as illustrated in the figures. It will be understood that the spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. For example, if the device in the figures is turned over, elements described as “below” or “beneath” other elements or features would then be oriented “above” the other elements or features. Thus, the exemplary term “below” can encompass both an orientation of above and below. The device may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein interpreted accordingly.

The terminology used herein is for the purpose of describing exemplary embodiments only and is not intended to be

limiting of the disclosed subject matter. As used herein, the singular forms “a”, “an”, and “the” are intended to include the plural forms as well, unless the context clearly indicates otherwise. It will be further understood that the terms “comprises” and/or “comprising,” when used in this specification, specify the presence of stated features, integers, steps, operations, elements, and/or components, but do not preclude the presence or addition of one or more other features, integers, steps, operations, elements, components, and/or groups thereof.

Exemplary embodiments of the disclosed subject matter are described herein with reference to cross-section illustrations that are schematic illustrations of idealized embodiments (and intermediate structures) of the disclosed subject matter. As such, variations from the shapes of the illustrations as a result, for example, of manufacturing techniques and/or tolerances, are to be expected. Thus, exemplary embodiments of the disclosed subject matter should not be construed as limited to the particular shapes of regions illustrated herein but are to include deviations in shapes that result, for example, from manufacturing.

Hereinafter, exemplary embodiments of the disclosed subject matter will be described in detail with reference to the accompanying drawings.

An OLED display according to exemplary embodiments of the present disclosure will now be described in detail with reference to FIGS. 1, 2, and 3.

FIG. 1 is a perspective view of an OLED display according to the exemplary is embodiments of the present disclosure. FIG. 2 is a side view of an OLED display according to exemplary embodiments of the present disclosure.

As shown in FIG. 1 and FIG. 2, an OLED display may include a front display part 10 configured to realize an image at a front side of the OLED display, a side display part 20 configured to realize an image at one or more side portions of the OLED display, and a bending display part 30 formed between the front display part 10 and the side display part 20. The bending display part 30 may be bent. The side portions of the OLED display including the side display part 20 may be formed at an angle (e.g., 90°) relative to the surface of the front side of the OLED display. The OLED display including the front display part 10, the bending display part 30, and the side display part 20 may be formed such that there is no dead space (i.e., space where an image is not realized).

As shown in FIG. 2, the front display part 10 may have a maximum luminance at a front side of the OLED display where the viewing angle ϕ is 0 degrees. The side display part 20 and the bending display part 30 may have maximum luminance at a viewing angle ϕ so that a user may easily view the side display part 20 and the bending display part 30. The viewing angle ϕ may be in a range from 5° to 70°.

A detailed structure of a pixel that may be used as a front pixel A1 formed at the front display part 10 and/or a side pixel A2 formed at the side display part 20 and the bending display part 30 is described with reference to FIGS. 3, 4, and 5.

FIG. 3 is an equivalent circuit of one pixel of the OLED display according to exemplary embodiments of the present disclosure. A pixel may refer to a minimum unit configured to display an image. The OLED display may include a plurality of pixels. The pixel in the OLED display may be implemented using various suitable structures. In some cases, the is pixel may include a plurality of TFTs and at least one capacitor. For example, as shown in FIG. 3, a 2Tr-1Cap structured active matrix (AM) type of OLED

display in which the pixel includes two thin film transistors (TFT) and one capacitor may be used.

As shown in FIG. 3, a pixel PX, representative of the front pixel A1 and the side pixel A2 of the OLED display, may include a plurality of signal lines 121, 171, and 172. A plurality of pixels PX may be connected to the signal lines 121, 171, and 172, and may be arranged in a matrix-like manner.

The signal lines 121, 171, and 172 include a scan line 121 configured to carry a scan signal (or a gate signal), a data line 171 configured to carry a data signal, and a driving voltage line 172 configured to carry a driving voltage ELVDD. The scan lines 121 run parallel with each other in a row direction, and the data lines 171 and the driving voltage lines 172 run parallel with each other in a column direction. The column direction may be approximately perpendicular to the row direction. The pixel PX includes a switching thin film transistor T1, a driving thin film transistor T2, a storage capacitor Cst, and an OLED.

The switching thin film transistor T1 has a control terminal, an input terminal, and an output terminal. The control terminal is connected to the scan line 121, the input terminal is connected to the data line 171, and the output terminal is connected to the driving thin film transistor T2. The switching thin film transistor T1 may provide a data signal applied to the data line 171 to the driving thin film transistor T2 when the switching thin film transistor T1 is turned on in response to a scan signal applied to the scan lines 121.

The driving thin film transistor T2 also has a control terminal, an input terminal, and an output terminal. The control terminal is connected to the output terminal of the switching thin film transistor T1, the input terminal is connected to the driving voltage line 172, and the output terminal is connected to the organic light emitting diode OLED. When the driving thin film transistor T2 is turned on, an output current I_d may flow and may vary in amplitude in accordance with a voltage applied between the control terminal and the output terminal of the driving thin film transistor T2.

The storage capacitor Cst is connected between the control terminal and input terminal of the driving thin film transistor T2. The storage capacitor Cst charges a data signal applied to the control terminal of the driving thin film transistor T2, and may maintain a voltage corresponding to a voltage level of the data signal after the switching thin film transistor T1 is turned off.

The organic light emitting diode OLED has an anode connected to the output terminal of the driving thin film transistor T2 and a cathode connected to a common voltage ELVSS. The organic light emitting diode OLED may display an image by emitting light with different intensities according to the output current I_d of the driving thin film transistor T2.

In some cases, the switching thin film transistor T1 and the driving thin film transistor T2 may be n-channel field effect transistors (FETs) or p-channel field effect transistors. However, it should be understood that the transistors T1 and T2 may be implanted using various types of transistors and that the transistors T1 and T2 are not limited to nFETs or pFETs. In addition, the connections among the thin film transistors T1 and T2, the storage capacitor Cst, and the organic light emitting diode OLED may vary.

A detailed structure of the front pixel A1 and the side pixel A2 of the OLED display will now be described in further detail with reference to FIGS. 3, 4, 5, and 6.

FIG. 4 is a layout view a front pixel A1 positioned at a front display part 10 and a side pixel A2 positioned at a side

display part 20 of the OLED display according to exemplary embodiments of the present disclosure. FIG. 5 is a cross-sectional view taken along the line V-V of FIG. 4, and FIG. 6 is a cross-sectional view taken along the line VI-VI of FIG. 4.

A buffer layer 120 may be formed on a substrate 110 of the front pixel A1 and the side pixel A2. The substrate 110 may be an insulating substrate made of glass, quartz, ceramic, or plastic. The buffer layer 120 may have a single-layered structure of silicon nitride (SiNx), or a double-layered structure of silicon nitride (SiNx) and silicon oxide (SiO₂). The buffer layer 120 may prevent unwanted components, such as impure elements or moisture, from intruding into the substrate 110, while simultaneously flattening a surface of the substrate 110.

A switching semiconductor layer 135a and a driving semiconductor layer 135b may be disposed on the buffer layer 120 and may be spaced apart from each other. These semiconductor layers 135a and 135b may be made of polysilicon or an oxide semiconductor. The oxide semiconductor may include a material selected from the group consisting of oxides based on titanium (Ti), hafnium (Hf), zirconium (Zr), aluminum (Al), tantalum (Ta), germanium (Ge), zinc (Zn), gallium (Ga), tin (Sn), or indium (In), and complex oxides thereof, such as zinc oxide (ZnO), indium-gallium-zinc oxide (InGaZnO₄), indium-zinc oxide (Zn—In—O), zinc-tin oxide (Zn—Sn—O), indium-gallium oxide (InGa—O), indium-tin oxide (In—Sn—O), indium-zirconium oxide (InZr—O), indium-zirconium-zinc oxide (InZr—Zn—O), indium-zirconium-tin oxide (In—Zr—Sn—O), indium-zirconium-gallium oxide (In—Zr—Ga—O), indium-aluminum oxide (In—Al—O), indium-zinc-aluminum oxide (In—Zn—Al—O), indium-tin-aluminum oxide (In—Sn—Al—O), indium-aluminum-gallium oxide (In—Al—Ga—O), indium-tantalum oxide (In—Ta—O), indium-tantalum-zinc oxide (In—Ta—Zn—O), indium-tantalum-tin oxide (In—Ta—Sn—O), indium-tantalum-gallium oxide (In—Ta—Ga—O), indium-germanium oxide (In—Ge—O), indium-germanium-zinc oxide (In—Ge—Zn—O), indium-germanium-tin oxide (In—Ge—Sn—O), indium-germanium-gallium oxide (In—Ge—Ga—O), titanium-indium-zinc oxide (Ti—In—Zn—O), and hafnium-indium-zinc oxide (Hf—In—Zn—O). If the semiconductor layers 135a and 135b are made of an oxide semiconductor, a separate protective layer may be added to protect the oxide semiconductor from external environmental elements, such as high temperature.

Each of the semiconductor layers 135a and 135b may include a channel region 1355 not doped with impurities, and source region 1356 and drain region 1357 formed of polysilicon doped with conductive impurities (e.g., impurity semiconductors) and formed at respective sides of the channel region 1355. The impurities vary according to the type of thin film transistor the semiconductor layers 135a and 135b are parts of, and may be N-type impurities or P-type impurities. For instance, if the transistor T1 is a nFET, the drain region 1357 and the source region 1356 of the semiconductor layer 135a may be doped with N-type impurities. If the transistor T1 is a pFET, the drain region 1357 and source region 1356 of the semiconductor layer 135a may be doped with p-type impurities.

A gate insulating film 140 is disposed on the switching semiconductor layer 135a, the driving semiconductor layer 135b, and the buffer layer 120. The gate insulating film 140 may be a single layer or a plurality of layers containing at least one of silicon nitride and silicon oxide.

The scan line **121**, a driving gate electrode **125b**, and a first storage capacitor plate **128** are formed on the gate insulating film **140**. The scan line **121** extends in a horizontal direction and may carry a scan signal. The scan line **121** may include a switching gate electrode **125a** protruding from the scan line **121** toward the switching semiconductor layer **135a**. The driving gate electrode **125b** may protrude from the first storage capacitor plate **128** toward the driving semiconductor layer **135b**. The switching gate electrode **125a** and the driving gate electrode **125b** overlap the channel regions **1355**, respectively.

An interlayer insulating film **160** is formed on the scan line **121**, the driving gate electrode **125b**, and the first storage capacitor plate **128**. The interlayer insulating film **160** may be formed of silicon nitride or silicon oxide.

Source contact holes **61** and drain contact holes **62** are formed in the interlayer insulating film **160** and the gate insulating film **140** to expose the source regions **1356** and the drain regions **1357**. Storage contact holes **63** are formed in the interlayer insulating film **160** to expose part of the first storage capacitor **128**.

A data line **171** having a switching source electrode **176a**, a driving voltage line **172** having a driving source electrode **176b** and a second storage capacitor plate **178**, and a switching drain electrode **177a** and a driving drain electrode **177b** that are connected to the first storage capacitor plate **128a** are formed on the interlayer insulating film **160**.

The data line **171** may carry a data signal, and may extend in a direction crossing the gate line **121**. The driving voltage line **172** may carry a driving voltage, may be separated from the data line **171**, and may extend in the same direction as the data line **171**.

The switching source electrode **176a** protrudes from the data line **171** toward the switching semiconductor layer **135a**, and the driving source electrode **176b** protrudes from the driving voltage line **172** toward the driving semiconductor layer **135b**. The switching source electrode **176a** and the source electrode **176b** are respectively connected to the source regions **1356** through the source contact holes **61**. The switching drain electrode **177a** faces the switching source electrode **176a**, the driving drain electrode **177b** faces the driving source electrode **176b**, and the switching drain electrode **177a** and the driving drain electrode **177b** are respectively connected to the drain regions **1357** through the drain contact holes **62**.

The switching drain electrode **177a** is extended and electrically connected to the first storage capacitor plate **128** through the storage contact hole **63** and the driving gate electrode **125b**.

The second storage capacitor plate **178** protrudes from the driving voltage line **171**, and overlaps the first storage capacitor plate **128**. Accordingly, the first storage capacitor plate **128** and the second storage capacitor plate **178** constitute the storage capacitor **Cst** by using the interlayer insulating film **160** as a dielectric material.

The switching semiconductor layer **135a**, the switching gate electrode **125a**, the switching source electrode **176a**, and the switching drain electrode **177a** constitute the switching thin film transistor **T1**, and the driving semiconductor layer **135b**, the driving gate electrode **125a**, the driving source electrode **176b**, and the driving drain electrode **177b** constitute the driving thin film transistor **T2**.

A protective layer **180** is disposed on the switching source electrode **176a**, the driving source electrode **176b**, the switching drain electrode **177a**, the driving drain electrode **177b**, and the second storage capacitor plate **178**. The protective layer **180** may be made of at least one material of

acryls resin (polyacrylates resin), epoxy resin, phenolic resin, polyamides resin, polyimides resin, unsaturated polyesters resin, polyphenylenethers resin, polyphenylenesulfides resin, and benzocyclobutene (BCB).

In some cases, as shown in FIG. **6**, an inclination groove **182** having an inclination angle θ may be formed at the protective layer **180** of the side pixel **A2**. In some cases, the inclination angle θ may be between 5° and 70° . However, it should be understood that various inclination angles may be possible.

A pixel electrode **710** may be disposed on the protective layer **180**, and may be formed at the inclination groove **182** of the protective layer **180** in the side pixel **A2** at an oblique angle (e.g., between 5° and 70°). The pixel electrode **710** may be made of a transparent conducting material, such as ITO (indium tin oxide), IZO (indium zinc oxide), ZnO (zinc oxide), or In_2O_3 (indium oxide), or a reflective metal such as lithium (Li), calcium (Ca), lithium fluoride/calcium (LiF/Ca), lithium fluoride/aluminum (LiF/Al), aluminum (Al), silver (Ag), magnesium (Mg), or gold (Au). The pixel electrode **710** may be electrically connected to the driving drain electrode **177b** of the driving thin film transistor **T2** through a contact hole **181** formed in the interlayer insulating film **160**, and may operate as an anode of the organic light emitting diode.

A pixel defining layer **350** may be disposed on edge portions of the pixel electrode **710** and the protective layer **180**. The pixel defining layer **350** may have an opening **351** exposing the pixel electrode **710**. The pixel defining layer **350** may be made of a resin such as polyacrylate resin or polyimide resin, a silica-based inorganic material, or the like.

An organic emission layer **720** may be disposed in the opening **351** of the pixel defining layer **350**. The organic emission layer **720** may be disposed on the pixel electrode **710** formed at the inclination groove **182** such that the organic emission layer **720** has the same inclination angle θ as the inclination angle θ of the pixel electrode **710**.

The organic emission layer **720** may include a plurality of layers including one or more of an emission layer, a hole injection layer (HIL), a hole transport layer (HTL), an electron transport layer (ETL), and an electron injection layer (EIL). When the organic emission layer **720** includes all of them, the hole injection layer (HIL) can be placed on the pixel electrode **710**, that is, the anode, and the hole transport layer (HTL), the emission layer, the electron transport layer (ETL), and the electron injection layer (EIL) can be sequentially stacked over the hole injection layer (HIL).

The organic emission layer **720** may include a red organic emission layer for emitting red light, a green organic emission layer for emitting green light, and a blue organic emission layer for emitting blue light. The red organic emission layer, the green organic emission layer, and the blue organic emission layer are respectively formed in red, green, and blue pixels, thereby displaying a color image.

In some cases, the red organic emission layer, green organic emission layer, and blue organic emission layer of the organic emission layer **720** may be respectively laminated on the red pixel, green pixel, and blue pixel, and a red color filter, a green color filter, and a blue color filter may be formed for the respective pixels, thereby displaying a color image. In some cases, a white organic emission layer for emitting white light may be formed on all of the red, green, and blue pixels, and a red color filter, a green color filter, and a blue color filter may be formed for the respective pixels, thereby displaying a color image. If the white organic

emission layer and the color filters are used to display a color image, there is no need to use a deposition mask for depositing the red, green, and blue organic emission layers on the respective pixels, i.e., the red, green, and blue pixels.

The white organic emission layer may be formed as one organic emission layer or a plurality of organic emission layers that are laminated to emit white light. For example, at least one yellow organic emission layer and at least one blue organic emission layer may be combined to emit white light, at least one cyan organic emission layer and at least one red organic emission layer may be combined to emit white light, or at least one magenta organic emission layer and at least one green organic emission layer may be combined to emit white light.

A common electrode **730** may be disposed on the pixel defining layer **350** and the organic emission layer **720**. The common electrode **730** may be disposed on the pixel electrode **710** and the organic emission layer **720** formed at the inclination groove **182** such that the common electrode **730** has the same inclination angle θ as the inclination angle θ of the pixel electrode **710**.

The common electrode **730** may be made of a transparent conducting material such as ITO (indium tin oxide), IZO (indium zinc oxide), ZnO (zinc oxide), or In_2O_3 (indium oxide), or a reflective metal such as lithium (Li), calcium (Ca), lithium fluoride/calcium (LiF/Ca), lithium fluoride/aluminum (LiF/Al), aluminum (Al), silver (Ag), magnesium (Mg), or gold (Au). The common electrode **730** may function as a cathode of the organic light emitting diode OLED. The pixel electrode **710**, the organic emission layer **720**, and the common electrode **730** constitute the side OLED **70**. The pixel electrode **710**, the organic emission layer **720**, and the common electrode **730** formed at the side pixel **A2** have the same inclination angle θ such that the surfaces thereof are parallel to each other. In some cases, the inclination angle θ may be between 5° and 70° . However, it should be understood that various inclination angles may be possible.

As described above, the side OLED **70** including the pixel electrode **710**, the organic emission layer **720**, and the common electrode **730** formed at the side pixel **A2** has the inclination angle θ such that the side display part **20** and the bending display part **30** formed at the side pixel **A2** may have the maximum luminance at the viewing angle ϕ .

A manufacturing method of the OLED display according to exemplary embodiments of the present disclosure will be described with reference to FIG. **5** and FIG. **6**.

As shown in FIG. **5** and FIG. **6**, the buffer layer **120** is disposed on the substrate **110** of the front pixel **A1** and the side pixel **A2**. In some cases, the buffer layer **120** may be disposed over the entire surface of the substrate **110** by a method such as plasma enhanced chemical vapor deposition (PECVD). Next, a semiconductor layer may be disposed on the buffer layer **120**. The semiconductor layer may be made of polysilicon or an oxide semiconductor, and the polysilicon may be formed by forming an amorphous silicon film and then crystallizing it. Various methods may be used to crystallize the amorphous silicon film. For example, the amorphous silicon film may be crystallized using heat, a laser, Joule heat, an electrical field, or a catalytic metal. Next, the semiconductor layer may be patterned by photolithography by using a first mask. In some cases, the switching semiconductor layer **135a** and the driving semiconductor layer **135b** may be simultaneously formed.

Next, the gate insulating film **140** may be disposed on the switching semiconductor layer **135a**, the driving semiconductor layer **135b**, and the buffer layer **120**. The gate insulating film **140** may be formed of silicon nitride (SiN_x)

or silicon oxide (SiO_2), and may be deposited over the entire surface of the buffer layer **120** by a method such as PECVD.

Next, a gate metal layer may be disposed on the gate insulating film **140**. The gate metal layer may be formed as a multilayer film in which a metal film including one of copper (Cu), a copper alloy, aluminum (Al), and an aluminum alloy and a metal film including either one of molybdenum (Mo) and a molybdenum alloy are laminated. Next, the gate metal layer may be patterned by photolithography using a second mask. As such, the switching gate electrode **125a** may be formed at a position overlapping the switching semiconductor layer **135**, the driving gate electrode **125b** may be formed at a position overlapping the driving semiconductor layer **135b**, and the first storage capacitor plate **128** may be connected to the driving gate electrode **125b**. Next, the switching semiconductor layer **135a** and the driving semiconductor layer **135b** may be doped with impurities, and may be divided into a channel region, a source region, and a drain region. The switching gate electrode **125a** and the driving gate electrode **125b** prevent the channel regions from being doped with impurities when the source regions and the drain regions are doped with impurities.

Next, an interlayer insulating film **160** may be disposed on the gate insulating film **140**, the switching gate electrode **125a**, and the driving gate electrode **125b**. The interlayer insulating film **160** may be an organic or inorganic film, and may be deposited over the entire surface of the substrate **110**. Next, the interlayer insulating film **160** and the gate insulating film **140** may be patterned by photolithography using a third mask to form a plurality of contact holes **61**, **62**, and **63**.

Next, a data metal layer may be disposed on the interlayer insulating film **160**. The data metal layer may be formed as a multilayer film in which a metal film including one of copper (Cu), a copper alloy, aluminum (Al), and an aluminum alloy and a metal film including either one of molybdenum (Mo) and a molybdenum alloy are laminated. For example, the data metal layer may be formed of a three-layered film of Mo/Al/Mo or a three-layered film of Mo/Cu/Mo.

Next, the data metal layer film may be patterned by photolithography using a fourth mask. As such, a data wire including the data line **171** having the switching source electrode **176a**, the driving voltage line **172** having the driving source electrode **176b** and the second storage capacitor plate **178**, and the switching drain electrode **177a** and the driving drain electrode **177b** that are connected to the first storage capacitor plate **128** are formed on the interlayer insulating film **160**.

Next, the protective layer **180** may be disposed on the interlayer insulating film **160** to cover the data wires **171**, **172**, **174**, **177a**, and **177b**. The contact hole **181** may be formed in the protective layer **180** in the front pixel **A1** and the side pixel **A2** by a photolithography process using a fifth mask; however, in the side pixel **A2**, the protective layer **180** is formed with the inclination groove **182** having inclination angle θ by photolithography using a gradual half tone mask part of the fifth mask.

Next, a pixel electrode layer may be disposed on the protective layer **180**, and the pixel electrode layer may be patterned by photolithography using a sixth mask to form the pixel electrode **710** connected to the driving drain electrode **177b** through the contact hole **181**. In the side pixel **A2**, the pixel electrode **710** is disposed on the inclination groove **182** is formed to have the inclination angle θ . A deposition speed, a deposition temperature, a deposition

voltage, and a deposition pressure of the pixel electrode layer may be controlled to form the pixel electrode 710 with a uniform thickness to be oblique.

Next, the pixel defining layer 350 may be disposed on the protective layer 180 to cover the pixel electrode 710, and the opening 351 is formed on the pixel defining film 350 by using a seventh mask to expose part of the pixel electrode 710.

The organic emission layer 720 may be disposed on the pixel electrode 710 in the opening 351 of the pixel defining layer 350, and the common electrode 730 may be disposed on the organic emission layer 720. The organic emission layer 720 and the common electrode 730 formed at the inclination groove 182 may have the inclination angle θ .

As described above, by forming the side OLED 70 including the pixel electrode 710, the organic emission layer 720, and the common electrode 730 to have the inclination angle θ at the side pixel A2, light emitted from the side display part 20 and the bending display part 30 in which the side pixel A2 is formed may have the maximum luminance at the viewing angle ϕ .

As described above, one inclination groove 182 may be formed at one side pixel A2 of the OLED display such that the side OLED 70 has one inclination angle. However, in some cases, a plurality of sub-inclination grooves may be formed in one side pixel A2 to have a plurality of inclination angles in the side OLED 70.

Next, referring to FIG. 7, an OLED display having a plurality of inclination angles will be described.

FIG. 7 is a cross-sectional view of a side pixel A2 positioned at a side display part 20 of an OLED display according to exemplary embodiments of the present disclosure.

The side pixel A2 of FIG. 7 is similar to the side pixel A2 of FIG. 6 except for a structure of the side OLED 70.

As shown in FIG. 7, at the protective layer 180 of the side pixel A2 of the OLED display, sub-inclination grooves 1821 and 1822 having an inclination angle θ_1 and an inclination angle θ_2 , respectively, may be formed at a region X1 and a region X2, respectively.

The pixel electrode 710 of the first electrode may be disposed on the protective layer 180, and the pixel electrode 710 formed at the sub-inclination grooves 1821 and 1822 of the protective layer 180 of the side pixel A2 may be oblique. The inclination angle θ_1 and the inclination angle θ_2 may be different from each other. The organic emission layer 720 of the side pixel A2 may be disposed on the pixel electrode 710 on the sub-inclination grooves 1821 and 1822 such that the organic emission layer 720 is formed with the inclination angle θ_1 and the inclination angle θ_2 . The common electrode 730 of the side pixel A2 may be disposed on the pixel electrode 710 and the organic emission layer 720 on the sub-inclination grooves 1821 and 1822, such that the common electrode 730 is formed with the inclination angle θ_1 and the inclination angle θ_2 .

As described above, the pixel electrode 710, the organic emission layer 720, and the common electrode 730 formed in the side pixel A2 may have an oblique inclination angle θ_1 and an oblique inclination angle θ_2 that are different from each other such that the maximum luminance may be obtained at viewing angles ϕ_1 and ϕ_2 inside the side pixel A2, which is formed in the side display part 20 and the bending display part 30.

In some cases, an inclination angle θ of the side OLED formed in a side red pixel, a side green pixel, and a side blue pixel may be different from each other.

Next, referring to FIG. 8, an OLED display with a side red pixel, a side green pixel, and a side blue pixel having different inclination angles θ will be described.

FIG. 8 is a cross-sectional view of a side red pixel, a side green pixel, and a side blue pixel of a side pixel A2 positioned at a side display part 20 of an OLED display according to exemplary embodiments of the present disclosure.

The side pixel A2 of FIG. 8 is similar to the side pixel A2 of FIG. 6 except for a structure of the side OLED 70.

As shown in FIG. 8, in the side pixel A2 of the OLED display, inclination grooves 182r, 182g, and 182b having different inclination angles θ_r , θ_g , and θ_b may be formed at the protective layer 180 of the side red pixel (R), the side green pixel (G), and the side blue pixel (B).

A pixel electrode 710 may be disposed on the protective layer 180 at the inclination grooves 182r, 182g, and 182b of the side red pixel (R), the side green pixel (G), and the side blue pixel (B), and may be oblique at different inclination angles θ_r , θ_g , and θ_b . The organic emission layer 720 of the side red pixel (R), the side green pixel (G), and the side blue pixel (B) may be disposed on the pixel electrode 710 at the different inclination angles θ_r , θ_g , and θ_b , respectively. The common electrode 730 of the side red pixel (R), the side green pixel (G), and the side blue pixel (B) may be disposed on the pixel electrode 710 and the organic emission layer 720 at the different inclination angles θ_r , θ_g , and θ_b , respectively.

As described above, the pixel electrode 710, the organic emission layer 720, and the common electrode 730 of side OLEDs 70 may be formed at the side red pixel (R), the side green pixel (G), and the side blue pixel (B), and may have different oblique inclination angles θ_r , θ_g , and θ_b such that the side red pixel (R), the side green pixel (G), and the side blue pixel (B) formed at the side display part 20 and the bending display part 30 may have the maximum luminance at the viewing angles ϕ_r , ϕ_g , and ϕ_b .

In some cases, the inclination angles θ_r , θ_g , and θ_b of the side OLED formed at the side red pixel (R), the side green pixel (G), and the side blue pixel (B) of the OLED display may be different from each other, and, in some cases, the inclination angles θ_r , θ_g , and θ_b may be the same. In some cases, the inclination angle θ of the side OLED formed in the side pixel A2 at the bending display part of the OLED display may be varied (e.g., gradually increased or decreased).

Referring to FIG. 9, an OLED display having varied inclination angles θ will be described.

FIG. 9 is a side view of an OLED display according to exemplary embodiments of the present disclosure.

As shown in FIG. 9, inclination angles θ_1 , θ_2 , and θ_3 of the side OLED formed at three adjacent side pixels A2 at the bending display part 30 of the OLED display may be gradually increased. The inclination angles θ_1 , θ_2 , and θ_3 may be increased such that three adjacent side pixels A2 formed at the bending display part 30 may have the maximum luminance at viewing angles ϕ_1 , ϕ_2 , and ϕ_3 .

In some cases, the inclination angles θ_1 , θ_2 , and θ_3 may be gradually decreased. In general, an inclination angle θ may vary according to the position of a pixel in the side display part 20 and the bending display part 30 in the OLED display. For example, the inclination angle of a pixel in the side display part may be different (e.g., smaller or larger) than an inclination angle of a pixel in the bending display part.

It will be apparent to those skilled in the art that various modifications and variations can be made in the present

disclosure without departing from the spirit or scope of the disclosed subject matter. Thus, it is intended that the present disclosure cover the modifications and variations of the disclosed subject matter provided they come within the scope of the appended claims and their equivalents.

What is claimed is:

1. An organic light emitting diode (OLED) display, comprising:

a front display part comprising a plurality of front pixels configured to provide an image at a first side of the OLED display; and

a side display part comprising a plurality of side pixels configured to provide the image at a second side of the OLED display,

wherein each of the plurality of side pixels comprises:

a plurality of thin film transistors;

a protective layer covering the plurality of thin film transistors and having an inclination groove such that a top surface of the protective layer is linearly oblique with respect to a bottom surface of the protective layer;

a first electrode disposed on the inclination groove;

a pixel defining layer disposed on the protective layer and having an opening exposing the first electrode;

an organic emission layer disposed on the first electrode and the pixel defining layer; and

a second electrode disposed on the organic emission layer,

wherein a side OLED comprises the first electrode, the organic emission layer, and the second electrode, and is configured to be oblique, and

wherein at least one of the side pixels comprises a side red pixel, a side green pixel, and a side blue pixel, inclination angles of the side red pixel, the side green pixel, and the side blue pixel being different from each other.

2. The OLED display of claim 1, wherein:

an inclination angle of the side OLED is in a range of 5 degrees to 70 degrees.

3. The OLED display of claim 2, wherein:

the inclination groove comprises a plurality of sub-inclination grooves having different inclination angles.

4. An organic light emitting diode (OLED) display, comprising:

a front display part comprising a plurality of front pixels configured to provide an image at a first side of the OLED display; and

a side display part comprising a plurality of side pixels configured to provide the image at a second side of the OLED display,

wherein each of the plurality of side pixels comprises:

a plurality of thin film transistors;

a protective layer covering the plurality of thin film transistors and having an inclination groove such that a top surface of the protective layer is linearly oblique with respect to a bottom surface of the protective layer;

a first electrode disposed on the inclination groove;

a pixel defining layer disposed on the protective layer and having an opening exposing the first electrode;

an organic emission layer disposed on the first electrode and the pixel defining layer; and

a second electrode disposed on the organic emission layer,

wherein a side OLED comprises the first electrode, the organic emission layer, and the second electrode, and is configured to be oblique, and

wherein the inclination angles of the side OLEDs sequentially increase or sequentially decrease based on positions of the side OLEDs.

5. A pixel, comprising:

a first pixel, a second pixel, and a third pixel configured to emit a color of light different from one another, each of the first, second, and third pixels comprising:

at least one switching element;

a protective layer disposed on the at least one switching element;

an organic light emitting diode (OLED) disposed on the protective layer, the OLED comprising a bottom electrode; and

a pixel defining layer disposed on the protective layer and comprising an opening that overlaps the bottom electrode of the OLED,

wherein an entire portion of the protective layer overlapping the opening is linearly inclined at an inclination angle relative to a bottom surface of the protective layer,

wherein the bottom electrode contacts with the top surface of the protective layer, is inclined at the inclination angle, and is connected to the at least one switching element, and

wherein the inclination angles of the bottom electrode of the first, second, and third pixels are different from one another.

6. The pixel of claim 5, wherein:

the OLED further comprises an organic emission layer disposed on the bottom electrode, and a second electrode disposed on the organic emission layer; and

the second electrode and the organic emission layer are inclined at the inclination angle.

7. The pixel of claim 5, wherein:

the inclination angle is oblique.

8. An organic light emitting diode (OLED) display, comprising:

a front display part;

a side display part; and

a bending display part connecting the front display part and the side display part,

wherein each of the front display part, the side display part, and the bending display part comprises a plurality of pixels, each of the plurality of pixels comprising at least one switching element, a protective layer disposed on the at least one switching element, and an OLED disposed on the protective layer,

wherein, in pixels of the front display part, a top surface of the OLED is parallel to a bottom surface of the protective layer, and

wherein, in a pixel of the side display part or the bending display part, a top surface of the protective layer is inclined at an inclination angle with respect to the bottom surface of the protective layer, and a top surface of the OLED is inclined with respect to the bottom surface of the protective layer.

9. The OLED display of claim 8, wherein:

in the pixel of the side display part or the bending display part, the protective layer comprises at least two inclination grooves corresponding to at least two inclination angles in the protective layer.

10. The OLED display of claim 8, wherein:

in the pixel of the side display part or the bending display part, a first portion of the top surface of the protective layer is inclined at a different angle than a second portion of the top surface of the protective layer;

a first portion of the top surface of the OLED is inclined at a different angle than a second portion of the top surface of OLED; and

the first portion of the top surface of the protective layer is parallel to the first portion of the top surface of the OLED.

11. The OLED display of claim 8, wherein:
the inclination angle comprises an oblique angle.
12. The OLED display of claim 8, wherein:
in adjacent pixels of the side display part or the bending
display part, the inclination angle is sequentially
increased or sequentially decreased.
13. The OLED display of claim 8, wherein:
the inclination angle of the protective layer in a pixel in
the side display part is different than the inclination
angle of the protective layer in a pixel in the bending
display part.
14. The OLED display of claim 8, wherein:
at least one pixel of the side display part or the bending
display part comprises a red pixel, a green pixel, and a
blue pixel;
the top surface of the protective layer in the red pixel is
inclined at a first inclination angle;
the top surface of the protective layer in the green pixel is
inclined at a second inclination angle; and
the top surface of the protective layer in the blue pixel is
inclined at a third inclination angle.
15. The OLED display of claim 14, wherein:
the first inclination angle, the second inclination angle,
and the third inclination angle are different from each
other.
16. An organic light emitting diode (OLED) display,
comprising:

- a front display part;
a side display part; and
a bending display part connecting the front display part
and the side display part,
wherein the front display part comprises a plurality of first
pixels, each of the plurality of first pixels comprising a
first OLED disposed on a first protective layer, the first
OLED forming a first inclination angle with respect to
a bottom surface of the first protective layer,
wherein each of the side display part and the bending
display part comprises a second OLED disposed on a
second protective layer, the second OLED forming a
second inclination angle with respect to a bottom
surface of the second protective layer,
wherein the first inclination angle is different from the
second inclination angle, and
wherein the second inclination angle corresponds to a
location of the second OLED.
17. The OLED display of claim 16, wherein:
the second OLED comprises a first electrode, an organic
emission layer, and a second electrode; and
the first electrode, the organic emission layer, and the
second electrode are oblique with respect to the bottom
surface of the second protective layer.

* * * * *

专利名称(译)	有机发光二极管显示器		
公开(公告)号	US9570527	公开(公告)日	2017-02-14
申请号	US14/063702	申请日	2013-10-25
[标]申请(专利权)人(译)	三星显示有限公司		
申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
[标]发明人	NAMKUNG JUN		
发明人	NAMKUNG, JUN		
IPC分类号	H01L27/32		
CPC分类号	H01L27/3258 H01L2251/5338 H01L51/0001 H01L51/0013 H01L51/56 H01L2251/56		
其他公开文献	US20150001477A1		
外部链接	Espacenet	USPTO	

摘要(译)

有机发光二极管显示器可以包括前显示部分，前显示部分包括形成在基板上并在前部和侧显示部分实现图像的多个前像素。侧面显示部的侧面像素可以包括：形成在基板上的多个薄膜晶体管；覆盖所述多个薄膜晶体管并且具有倾斜的倾斜槽的保护层；形成在所述保护层的倾斜槽处的第一电极；像素限定层，具有暴露所述第一电极并形成在所述保护层上的开口；有机发射层，形成在所述第一电极和所述像素限定层上；和覆盖有机发射层的第二电极。

